



GP
ELECTRONICS

GP01N15

150V N-Channel MOSFET

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)}TYP$	I_D
150V	430m Ω @10V	1A

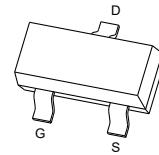
Feature

- Trench Technology Power MOSFET
- Low $R_{DS(ON)}$
- Low Gate Charge

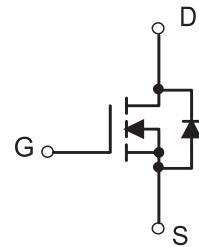
Application

- Load Switching
- Low Current Inverters
- Low Current DC/DC Converters

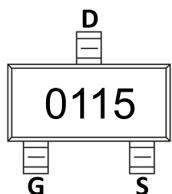
SOT-23



Schematic diagram



MARKING:



ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain - Source Voltage	V_{DS}	150	V
Gate - Source Voltage	V_{GS}	± 20	V
Continuous Drain Current ^{1,5}	I_D	1	A
Pulsed Drain Current ²	I_{DM}	4	A
Power Dissipation ^{4,5}	P_D	0.4	W
Thermal Resistance from Junction to Ambient ⁵	$R_{\theta JA}$	312	°C/W
Junction Temperature	T_J	150	°C
Storage Temperature	T_{STG}	-55~+150	°C

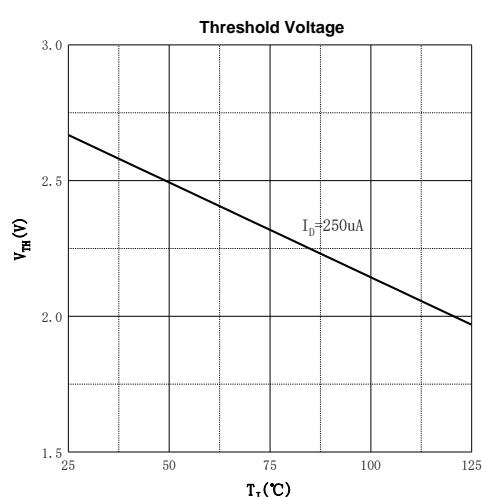
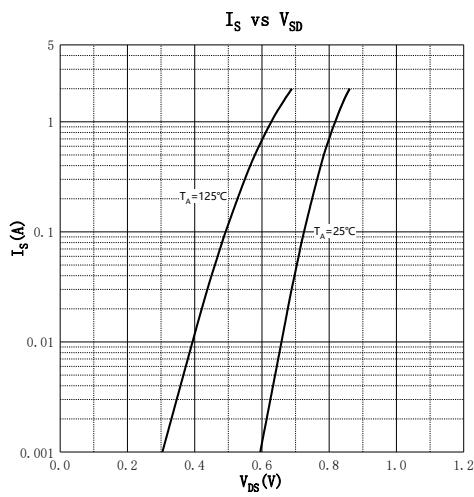
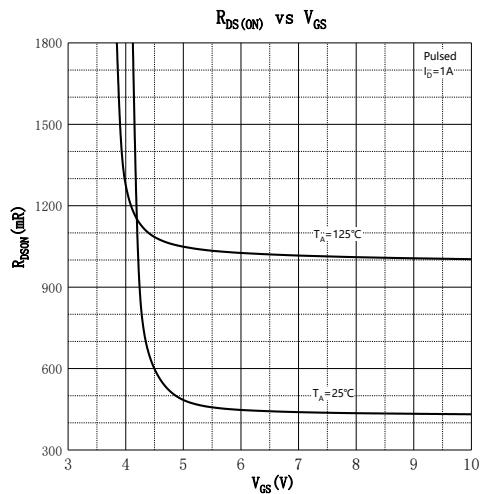
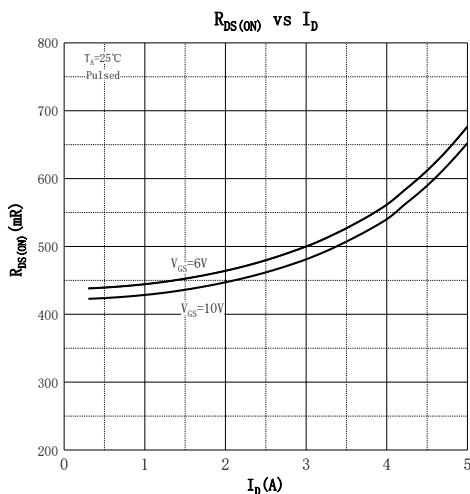
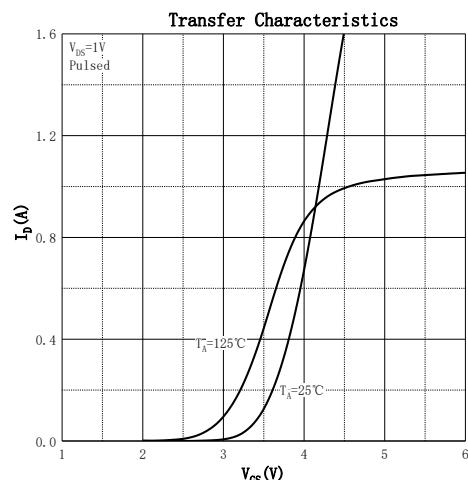
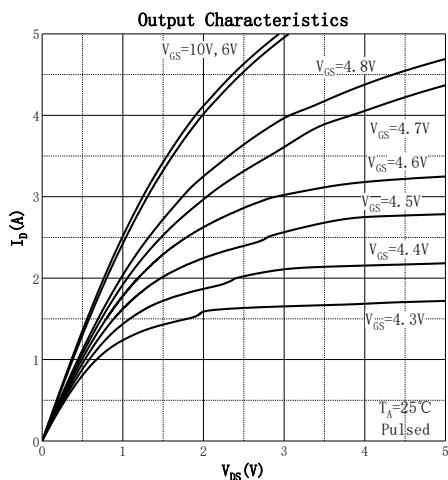
MOSFET ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

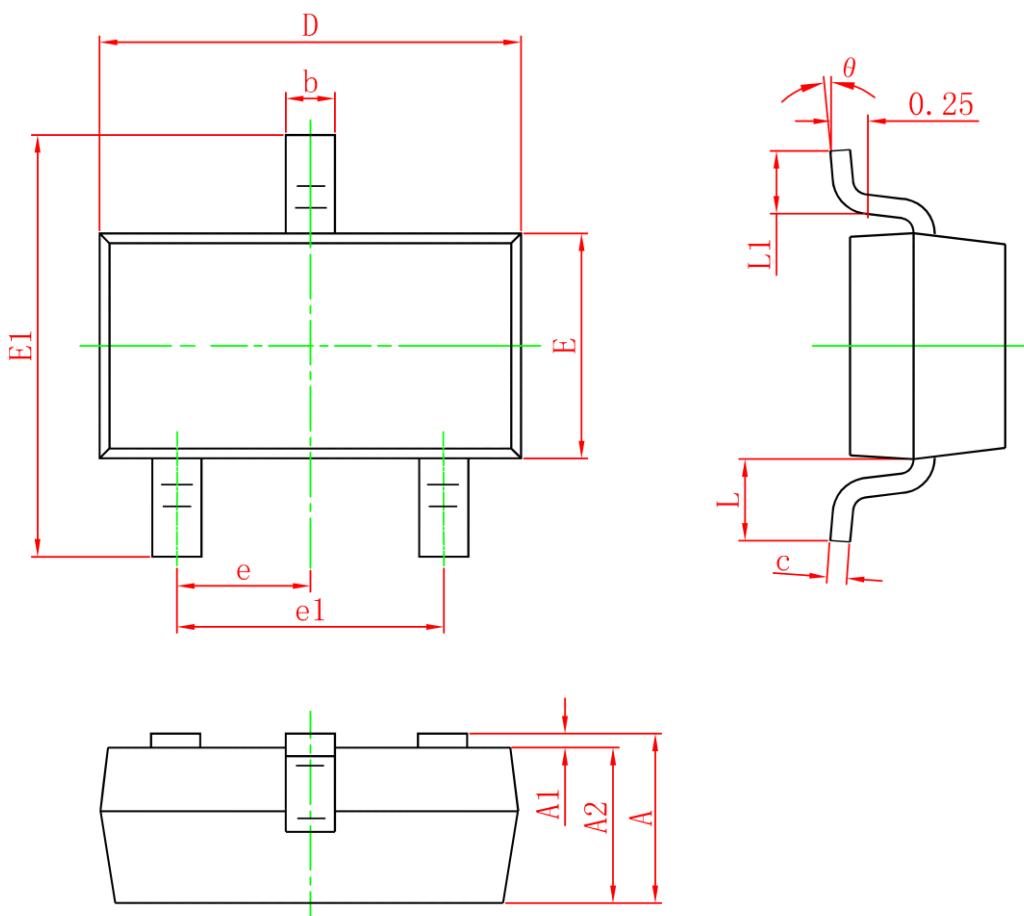
Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Off Characteristics						
Drain - Source Breakdown Voltage	$V_{(\text{BR})\text{DSS}}$	$V_{\text{GS}} = 0\text{V}, I_D = 250\mu\text{A}$	150			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{\text{DS}} = 120\text{V}, V_{\text{GS}} = 0\text{V}$			-1	μA
Gate - Body Leakage Current	I_{GSS}	$V_{\text{GS}} = \pm 20\text{V}, V_{\text{DS}} = 0\text{V}$			± 100	nA
On Characteristics³						
Gate Threshold Voltage	$V_{\text{GS}(\text{th})}$	$V_{\text{DS}} = V_{\text{GS}}, I_D = 250\mu\text{A}$	1.5	2.5	3.5	V
Drain-source On-resistance	$R_{\text{DS}(\text{on})}$	$V_{\text{GS}} = 10\text{V}, I_D = 1\text{A}$		430	650	$\text{m}\Omega$
Forward Transconductance	g_{FS}	$V_{\text{DS}} = 5\text{V}, I_D = 1\text{A}$		2		S
Dynamic Characteristics						
Input Capacitance	C_{iss}	$V_{\text{DS}} = 45\text{V}, V_{\text{GS}} = 0\text{V}, f = 1\text{MHz}$		372		pF
Output Capacitance	C_{oss}			14		
Reverse Transfer Capacitance	C_{rss}			11		
Switching Characteristics						
Total Gate Charge	Q_g	$V_{\text{DS}} = 75\text{V}, V_{\text{GS}} = 10\text{V}, I_D = 1\text{A}$		8.7		nC
Gate-source Charge	Q_{gs}			0.79		
Gate-drain Charge	Q_{gd}			2.7		
Turn-on Delay Time	$t_{\text{d}(\text{on})}$	$V_{\text{DD}} = 75\text{V}, V_{\text{GS}} = 10\text{V}, R_L = 75\Omega, R_G = 3\Omega$		8		ns
Turn-on Rise Time	t_r			22		
Turn-off Delay Ttime	$t_{\text{d}(\text{off})}$			9		
Turn-off Fall Time	t_f			20		
Source - Drain Diode Characteristics						
Diode Forward Voltage ³	V_{SD}	$V_{\text{GS}} = 0\text{V}, I_s = 1\text{A}$			1.2	V

Notes :

- 1.The maximum current rating is limited by package.
- 2.Repetitive rating:pulse width limited by $T_{J(\text{MAX})} = 150^\circ\text{C}$.
- 3.Pulse Test : Pulse Width $\leq 300\mu\text{s}$, duty cycle $\leq 2\%$.
- 4.The power dissipation PD is limited by $T_{J(\text{MAX})} = 150^\circ\text{C}$.
- 5.Device mounted on 1in2 FR-4 board with 2oz. Copper, in a still air environment with $T_A = 25^\circ\text{C}$.

Typical Characteristics



SOT-23 Package Information


Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.150	0.035	0.045
A1	0	0.100	0	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.150	1.500	0.045	0.059
E1	2.250	2.650	0.089	0.104
e	0.950TYP		0.037TYP	
e1	1.800	2.000	0.071	0.079
L	0.550REF		0.022REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°